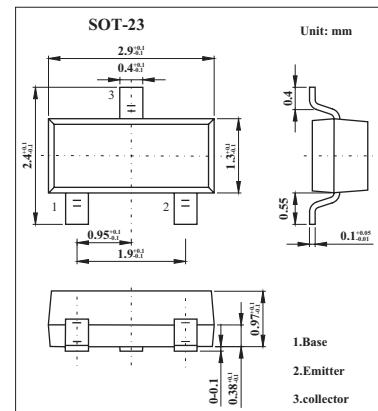
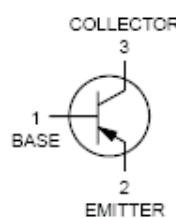


NPN General Purpose Amplifier

MMBT5088, MMBT5089

■ Features

- NPN general purpose amplifier



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	MMBT5088	MMBT5089	Unit
Collector-emitter voltage	V _{CES}	30	25	V
Collector-base voltage	V _{CBO}	35	30	V
Emitter-base voltage	V _{EBO}		4.5	V
Collector current	I _C		100	mA
Junction temperature	T _j		150	°C
Storage temperature	T _{stg}	-55 to +150		°C
Total device dissipation	P _D	625	350	mW
Derate above 25°C		5.0	2.8	mW/°C
Thermal resistance, junction to case	R _{θJC}	83.3		°C/W
Thermal resistance, junction to ambient	R _{θJA}	200	357	°C/W

MMBT5088, MMBT5089

■ Electrical Characteristics Ta = 25°C unless otherwise noted

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage MMBT5088 MMBT5089	V _{(BR)CEO}	I _C = 1.0 mA, I _B = 0	30			V
			25			
Collector-base breakdown voltage MMBT5088 MMBT5089	V _{(BR)CBO}	I _C = 100 µA, I _E = 0	35			V
			30			
Collector-cutoff current MMBT5088 MMBT5089	I _{CBO}	V _{CB} = 20 V, I _E = 0			50	nA
		V _{CB} = 15 V, I _E = 0			50	nA
Emitter-base cut-off current	I _{EBO}	V _{EB} = 3.0 V, I _C = 0			50	nA
		V _{EB} = 4.5 V, I _C = 0			100	nA
DC current gain MMBT5088 MMBT5089	h _{FE}	I _C = 100 µA, V _{CE} = 5.0 V	300		900	
			400		1200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10 mA, I _B = 1.0 mA			0.5	V
Base-emitter saturation voltage	V _{BE(on)}	I _C = 10 mA, V _{CE} = 5.0 V			0.8	V
Current gain - bandwidth product	f _T	I _C = 500 µA, V _{CE} = 5.0 mA, f = 20 MHz	50			MHz
Collector-base capacitance	C _{cb}	V _{CB} = 5.0 V, I _E = 0, f = 100 KHz			4.0	pF
Emitter-base capacitance	C _{eb}	V _{BE} = 0.5 V, I _C = 0, f = 100 KHz			10	pF
Small-signal current gain MMBT5088 MMBT5089	h _{fe}	I _C = 1.0 mA, V _{CE} = 5.0 V, f = 1.0 KHz	350		1400	
			450		1800	
Noise figure MMBT5088 MMBT5089	NF	I _C = 100 µA, V _{CE} = 5.0 V, R _S = 10KΩ, f = 10 Hz to 15.7kHz			3.0	dB
					2.0	dB

■ hFE Classification

TYPE	MMBT5088	MMBT5089
Marking	1Q	1R